

The invention relates to material engineering and can be used in radioelectronics, semiconductor and optoelectronic instrument making, in particular in manufacturing infrared devices. Disclosed is a method for reducing concentration of acceptors in crystals with native defects, in which crystals are grown using Bridgman vertical method or solid-state recrystallization, moreover the middle part of the grown crystal is cut; the manufactured crystals are cut in the form of parallelepiped with dimensions of $(2 \times 2 \times 6)$ mm, mechanically finished and chemically polished in bromine-mentol etchant 5 % Br_2 + 95 % CH_3OH , and deformed by a dynamic loading along a long rib under the room temperature up to relative deformation $\varepsilon \leq 2\%$, thereafter the deformed layer enriched with dislocations is chemically etched for a thickness of 100-200 μm . The technical result of the invention is reducing concentration of acceptors in crystals with native defects.